

# Infrared light emitting diode, top view type

## SIR-320ST3F

The SIR-320ST3F is a GaAs infrared light emitting diode housed in clear plastic. This device has a high luminous efficiency and a 940 nm spectrum suitable for silicon detectors. It is small and at the same time has a wide radiation angle, making it ideal for compact optical control equipment.

### ● Applications

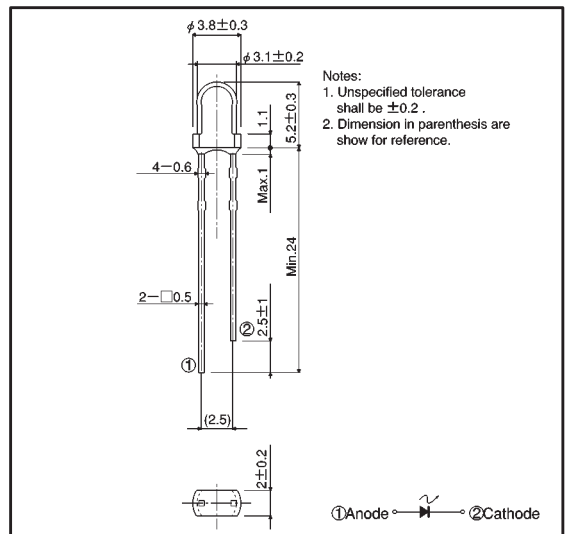
Optical control equipment

Light source for remote control devices

### ● Features

- 1) Compact ( $\phi 3.1$  mm).
- 2) High efficiency, high output  $P_o = 9.0$  mW ( $I_F = 50$  mA).
- 3) Wide radiation angle  $\theta = \pm 18^\circ$ .
- 4) Emission spectrum well suited to silicon detectors ( $\lambda_P = 940$  nm).
- 5) Good current-optical output linearity.
- 6) Long life, high reliability.
- 7) Low cost, clear epoxy resin package.

### ● External dimensions (Units: mm)



### ● Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

| Parameter             | Symbol     | Limits         | Unit             |
|-----------------------|------------|----------------|------------------|
| Forward current       | $I_F$      | 75             | mA               |
| Reverse voltage       | $V_R$      | 5              | V                |
| Power dissipation     | $P_D$      | 100            | mW               |
| Pulse forward current | $I_{FP}^*$ | 1.0            | A                |
| Operating temperature | $T_{opr}$  | $-25 \sim +85$ | $^\circ\text{C}$ |
| Storage temperature   | $T_{stg}$  | $-40 \sim +85$ | $^\circ\text{C}$ |

\* Pulse width = 0.1 msec, duty ratio 1%

## ●Electrical and optical characteristics (Ta = 25°C)

| Parameter                      | Symbol           | Min. | Typ. | Max. | Unit  | Conditions           |
|--------------------------------|------------------|------|------|------|-------|----------------------|
| Optical output                 | P <sub>O</sub>   | —    | 9.0  | —    | mW    | I <sub>F</sub> =50mA |
| Emitting strength              | I <sub>E</sub>   | 5.6  | —    | —    | mW/sr | I <sub>F</sub> =50mA |
| Forward voltage                | V <sub>F</sub>   | —    | 1.2  | 1.5  | V     | I <sub>F</sub> =50mA |
| Reverse current                | I <sub>R</sub>   | —    | —    | 10   | μA    | V <sub>R</sub> =3V   |
| Peak light emitting wavelength | λ <sub>P</sub>   | —    | 940  | —    | nm    | I <sub>F</sub> =50mA |
| Spectral line half width       | Δλ               | —    | 40   | —    | nm    | I <sub>F</sub> =50mA |
| Half-viewing angle             | θ <sub>1/2</sub> | —    | ±18  | —    | deg   | I <sub>F</sub> =50mA |
| Response time                  | tr · tf          | —    | 1.0  | —    | μs    | I <sub>F</sub> =50mA |
| Cut-off frequency              | fc               | —    | 1.0  | —    | MHz   | I <sub>F</sub> =50mA |

## ●Electrical and optical characteristic curves

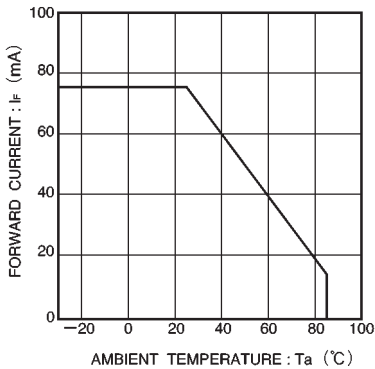


Fig. 1 Forward current falloff

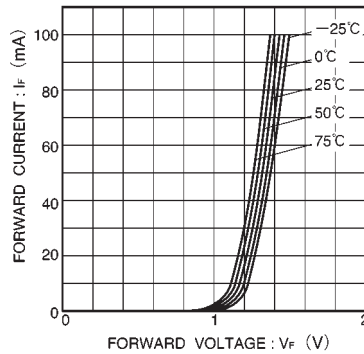


Fig. 2 Forward current vs. forward voltage

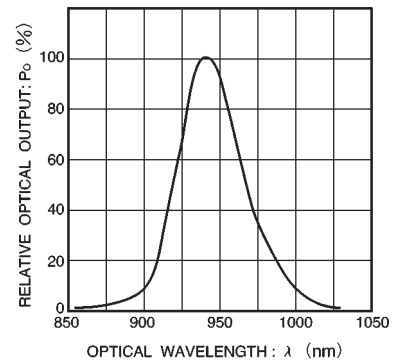


Fig. 3 Wavelength

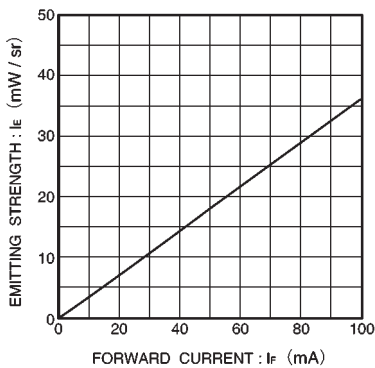


Fig. 4 Emitting strength vs. forward current

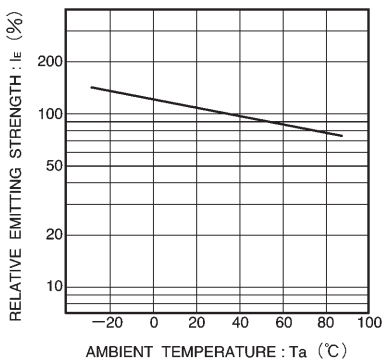


Fig. 5 Radiant intensity vs. ambient temperature

## ● Directional pattern

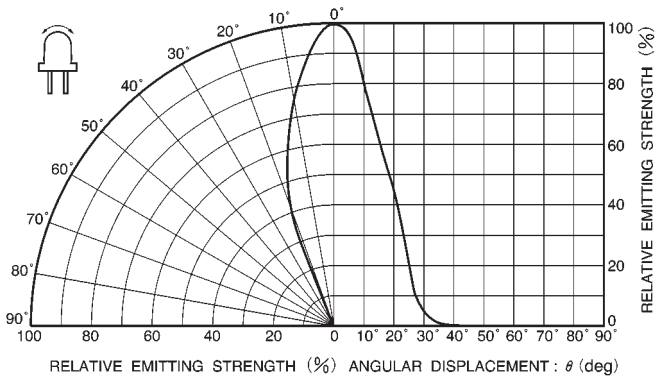


Fig. 6 Directional pattern

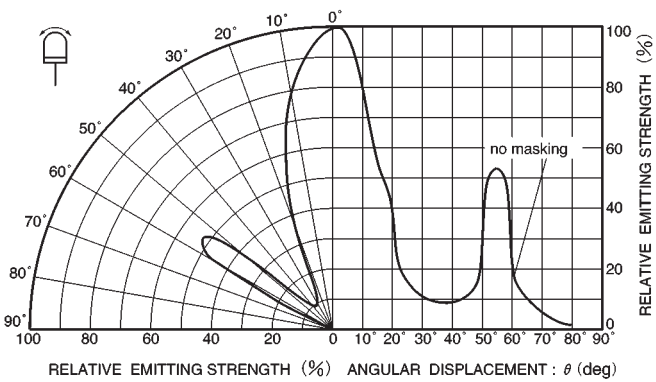


Fig. 7 Directional pattern